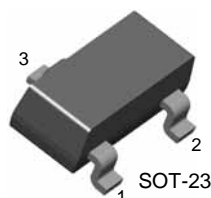


MMBT3904K

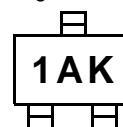
NPN Epitaxial Silicon Transistor

General Purpose Transistor



1. Base 2. Emitter 3. Collector

Marking



Absolute Maximum Ratings $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	200	mA
P_C	Collector Power Dissipation	350	mW
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 ~ 150	$^\circ\text{C}$

Electrical Characteristics $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 10\mu\text{A}, I_E = 0$	60		V
BV_{CEO}	Collector-Emitter Breakdown Voltage *	$I_C = 1\text{mA}, I_B = 0$	40		V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 10\mu\text{A}, I_C = 0$	6		V
I_{CEX}	Collector Cut-off Current	$V_{CE} = 30\text{V}, V_{EB} = 3\text{V}$		50	nA
h_{FE}	DC Current Gain *	$V_{CE} = 1\text{V}, I_C = 0.1\text{mA}$ $V_{CE} = 1\text{V}, I_C = 1\text{mA}$ $V_{CE} = 1\text{V}, I_C = 10\text{mA}$ $V_{CE} = 1\text{V}, I_C = 50\text{mA}$ $V_{CE} = 1\text{V}, I_C = 100\text{mA}$	40 70 100 60 30	300	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage *	$I_C = 10\text{mA}, I_B = 1\text{mA}$ $I_C = 50\text{mA}, I_B = 5\text{mA}$		0.2 0.3	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage *	$I_C = 10\text{mA}, I_B = 1\text{mA}$ $I_C = 50\text{mA}, I_B = 5\text{mA}$	0.65	0.85 0.95	V V
C_{ob}	Output Capacitance	$V_{CB} = 5\text{V}, I_E = 0, f = 1\text{MHz}$		4	pF
f_T	Current Gain-Bandwidth Product	$V_{CE} = 20\text{V}, I_C = 10\text{mA}, f = 100\text{MHz}$	300		MHz
NF	Noise Figure	$I_C = 100\mu\text{A}, V_{CE} = 5\text{V}, R_S = 1\text{K}\Omega$ $f = 10\text{Hz to } 15.7\text{KHz}$		5	dB
t_{ON}	Turn On Time	$V_{CC} = 3\text{V}, V_{BE} = 0.5\text{V}$ $I_C = 10\text{mA}, I_{B1} = 1\text{mA}$		70	ns
t_{OFF}	Turn Off Time	$V_{CC} = 3\text{V}, I_C = 10\text{mA}, I_{B1} = I_{B2} = 1\text{mA}$		250	ns

* Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Typical Performance Characteristics

Figure 1. DC current Gain

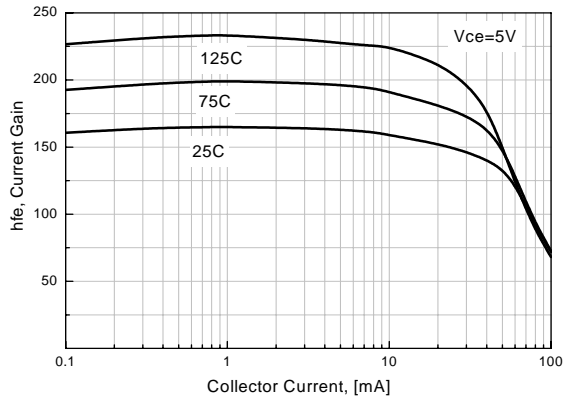


Figure 2. Collector-Emitter Saturation Voltage

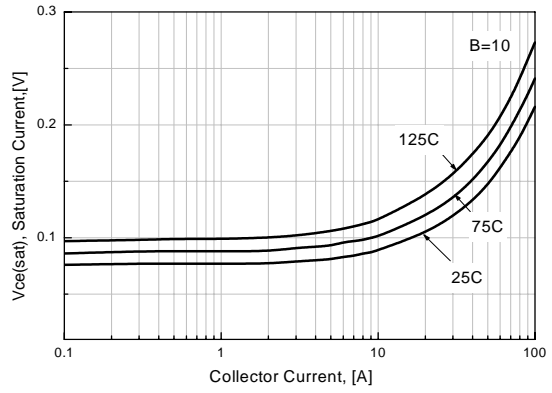


Figure 3. Base-Emitter Saturation Voltage

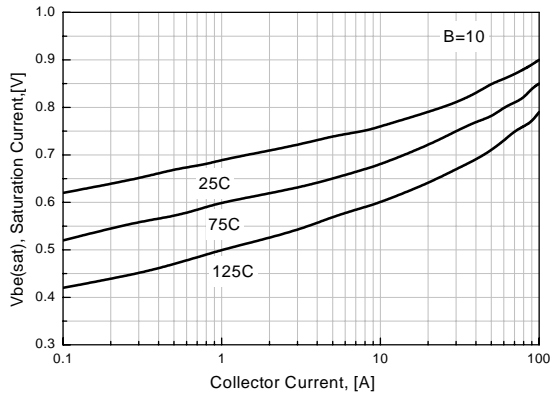


Figure 4. Collector - Base Leakage Current

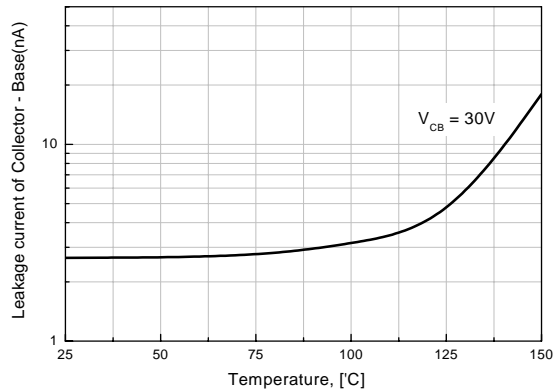


Figure 5. Output Capacitance

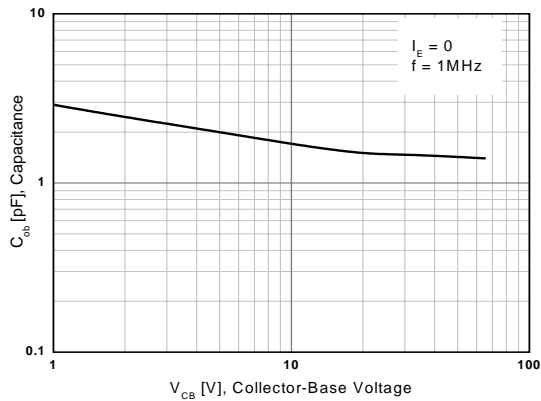
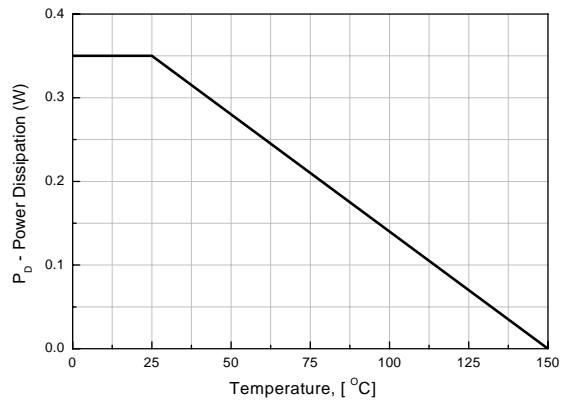
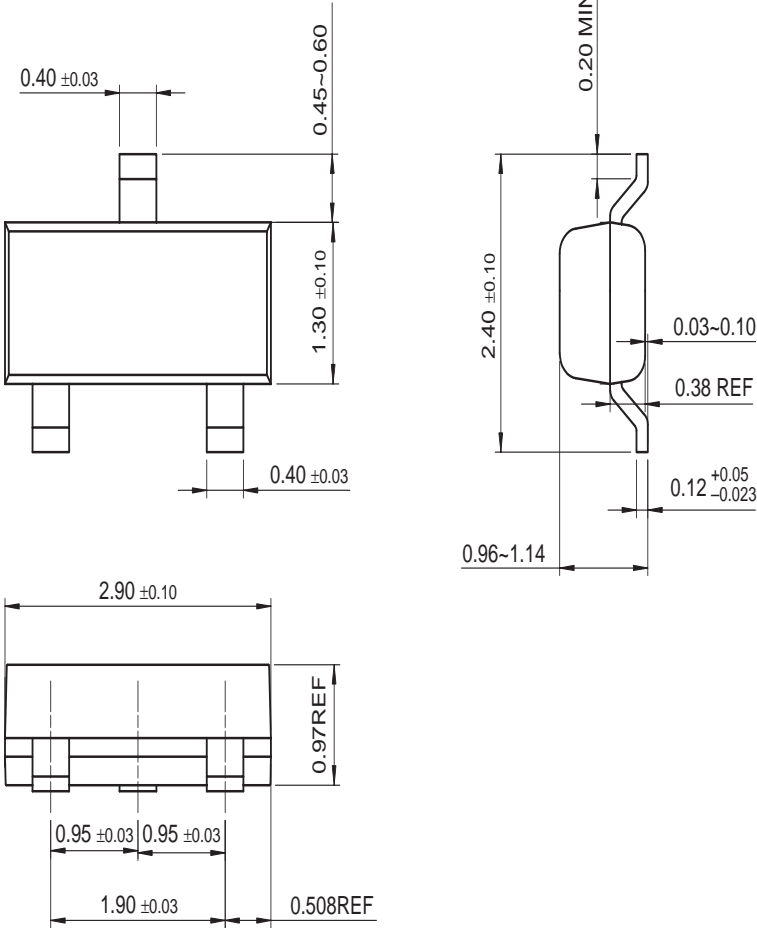


Figure 6. Power Dissipation vs Ambient Temperature



Mechanical Dimensions

SOT-23



Dimensions in Millimeters

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EnSigna TM	ImpliedDisconnect TM	OCXPro TM	ScalarPump TM	VCX TM
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FACT Quiet Series TM		OPTOPLANAR TM	SMART START TM	
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Programmable Active Droop TM		Power247 TM	SuperFET TM	
		PowerEdge TM	SuperSOT TM -3	

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